

# CR6PM-12

## Thyristor

Medium Power Use

REJ03G0358-0100

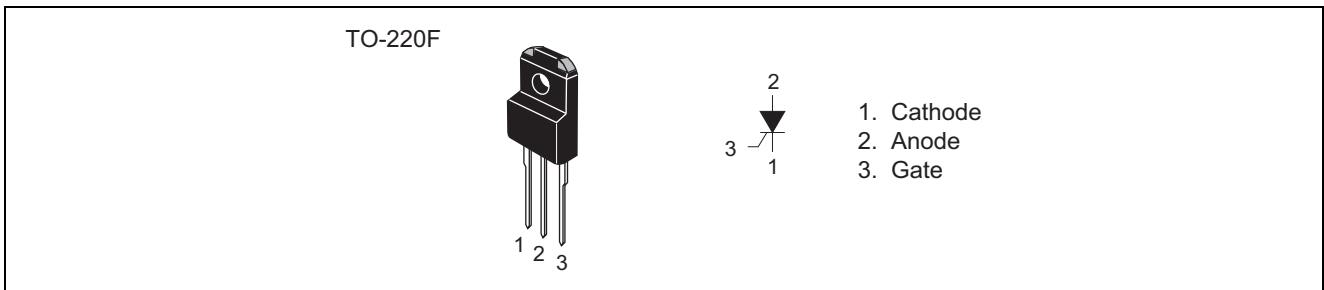
Rev.1.00

Aug.20.2004

### Features

- $I_{T(AV)}$  : 6 A
- $V_{DRM}$  : 600 V
- $I_{GT}$  : 10 mA
- $V_{ISO}$  : 1500V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904  
File No. E80271

### Outline



### Applications

Switching mode power supply, regulator for autcycle, motor control, heater control, and other general purpose control applications

### Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak reverse voltage	$V_{RRM}$	600	V
Non-repetitive peak reverse voltage	$V_{RSM}$	720	V
DC reverse voltage	$V_{R(DC)}$	480	V
Repetitive peak off-state voltage	$V_{DRM}$	600	V
DC off-state voltage	$V_{D(DC)}$	480	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	9.4	A	
Average on-state current	$I_{T(AV)}$	6	A	Commercial frequency, sine half wave 180° conduction, $T_c = 85^\circ\text{C}$
Surge on-state current	$I_{TSM}$	90	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusing	$I^2t$	34	$\text{A}^2\text{s}$	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate forward voltage	$V_{FGM}$	6	V	
Peak gate reverse voltage	$V_{RGM}$	10	V	
Peak gate forward current	$I_{FGM}$	2	A	
Junction temperature	$T_j$	- 40 to +125	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	- 40 to +125	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	1500	V	$T_a = 25^\circ\text{C}$ , AC 1 minute, each terminal to case

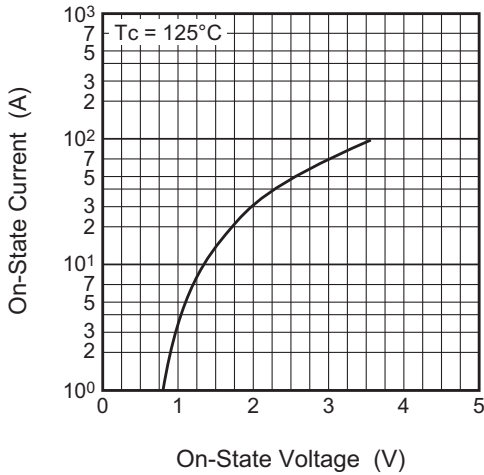
## Electrical Characteristics

Parameter	Symbol	Rated value			Unit	Test conditions
		Min.	Typ.	Max.		
Repetitive peak reverse current	$I_{RRM}$	—	—	2.0	mA	$T_j = 125^\circ\text{C}$ , $V_{RRM}$ applied
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 125^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.7	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 20\text{ A}$ , instantaneous value
Gate trigger voltage	$V_{GT}$	—	—	1.0	V	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $I_T = 1\text{ A}$
Gate non-trigger voltage	$V_{GD}$	0.2	—	—	V	$T_j = 125^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Gate trigger current	$I_{GT}$	—	—	10	mA	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $I_T = 1\text{ A}$
Holding current	$I_H$	—	15	—	mA	$T_j = 25^\circ\text{C}$ , $V_D = 12\text{ V}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.0	$^\circ\text{C/W}$	Junction to case <sup>Note1</sup>

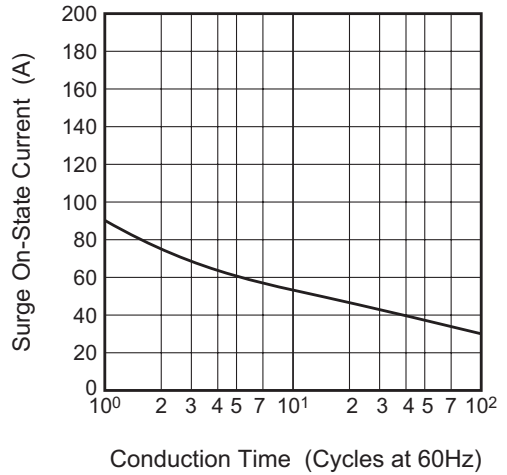
Notes: 1. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C/W}$ .

Performance Curves

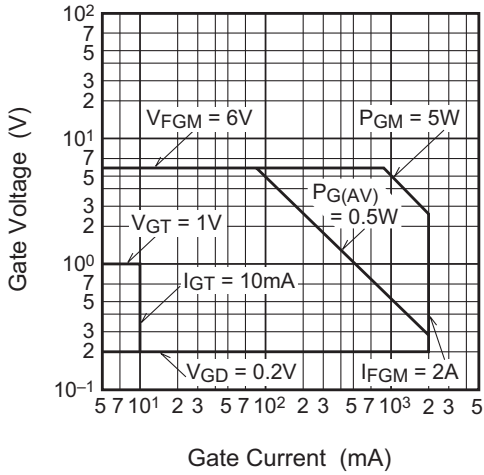
Maximum On-State Characteristics



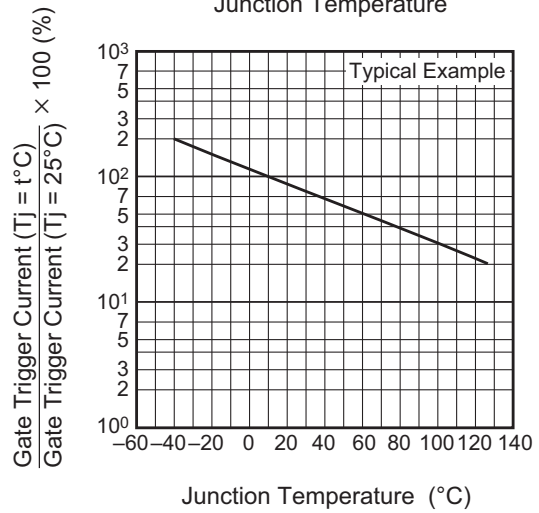
Rated Surge On-State Current



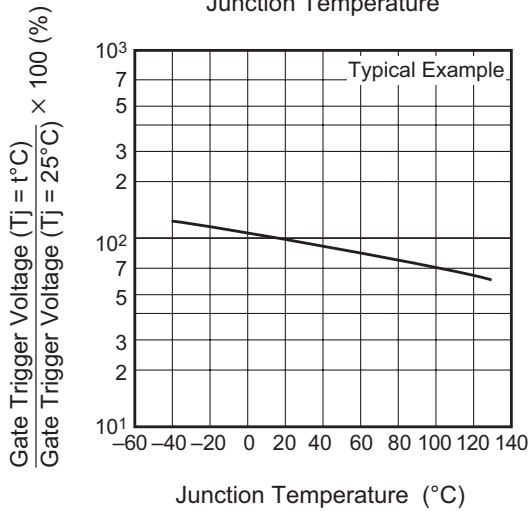
Gate Characteristics



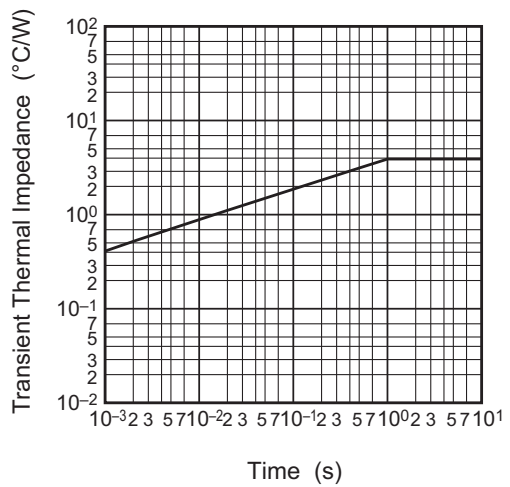
Gate Trigger Current vs. Junction Temperature

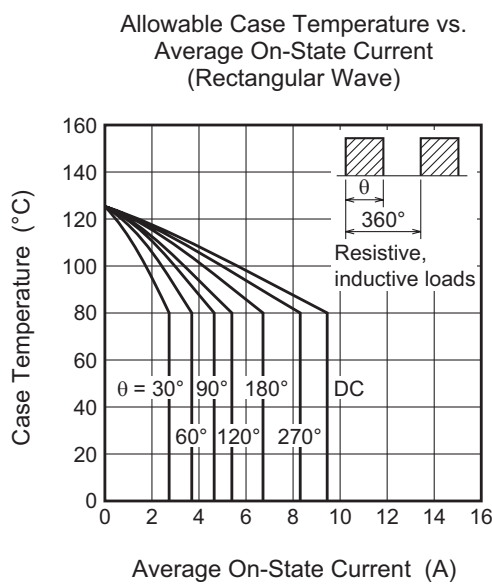
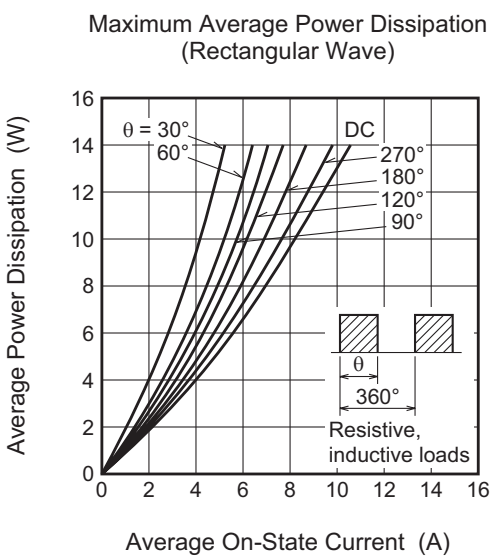
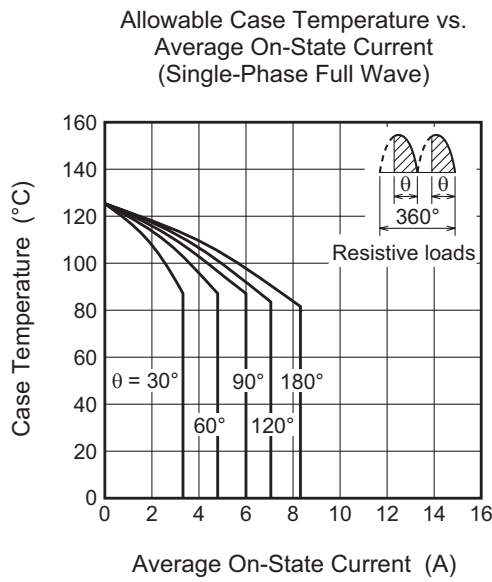
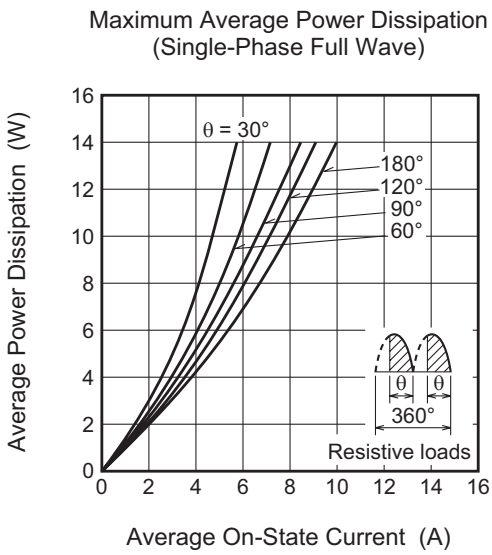
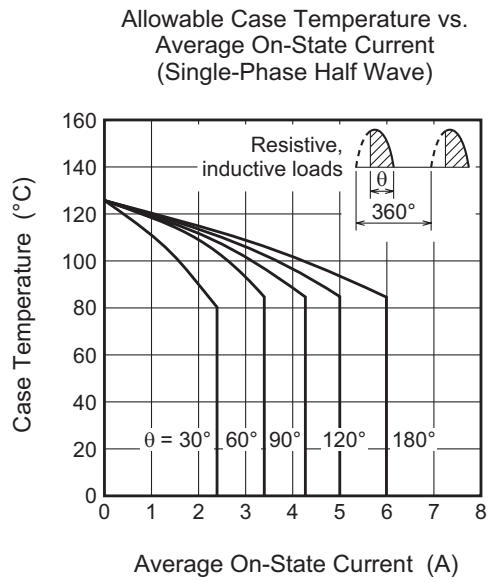
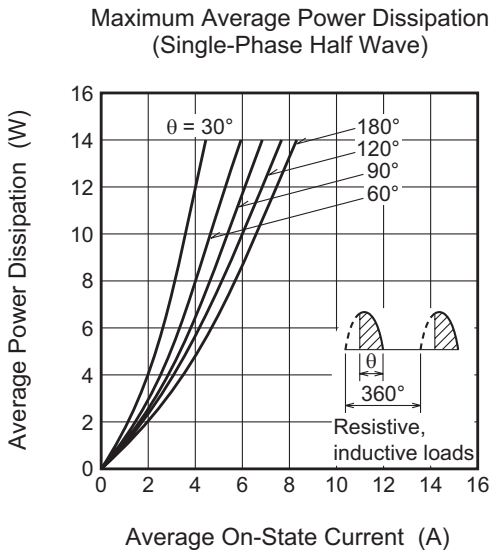


Gate Trigger Voltage vs. Junction Temperature

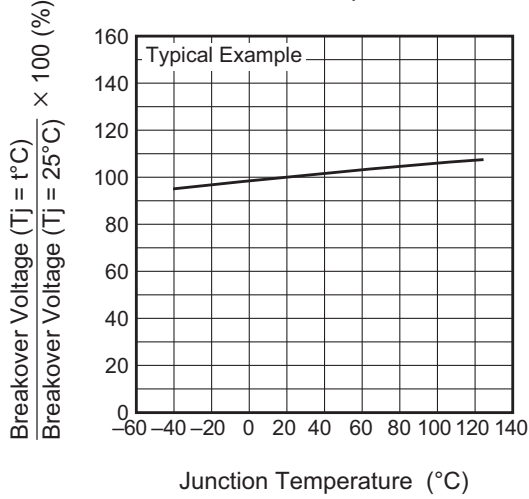


Maximum Transient Thermal Impedance Characteristics (Junction to case)

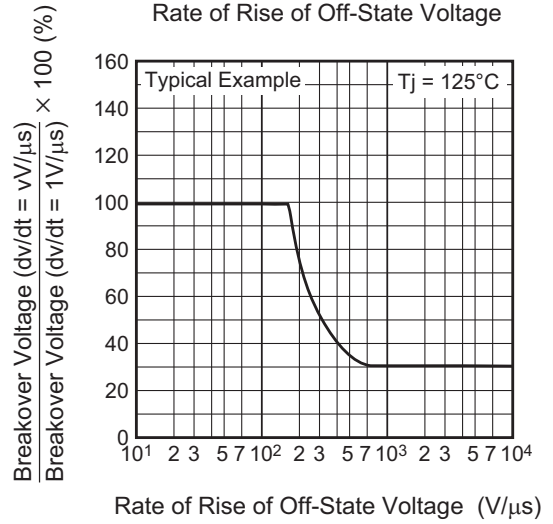




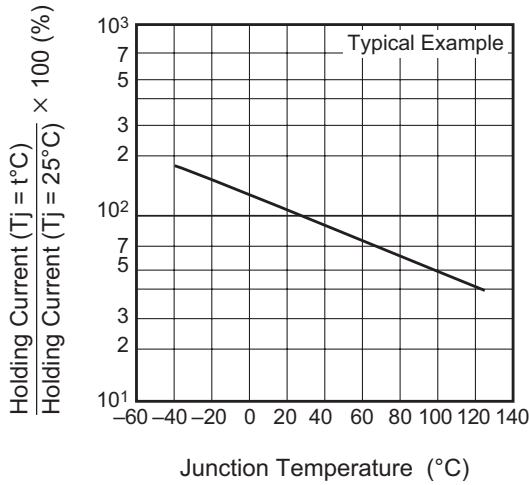
Breakover Voltage vs. Junction Temperature



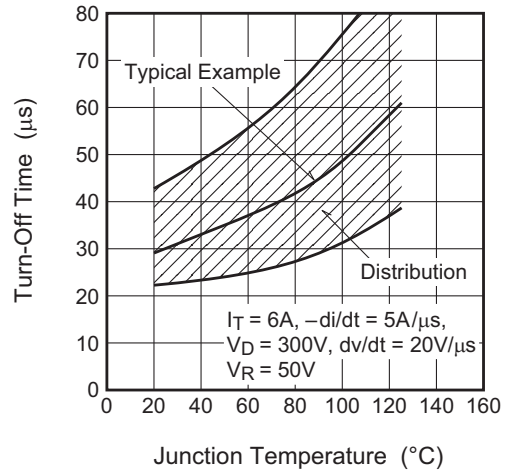
Breakover Voltage vs. Rate of Rise of Off-State Voltage



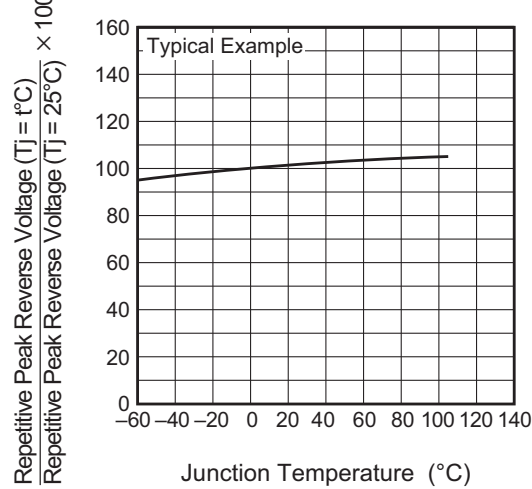
Holding Current vs. Junction Temperature



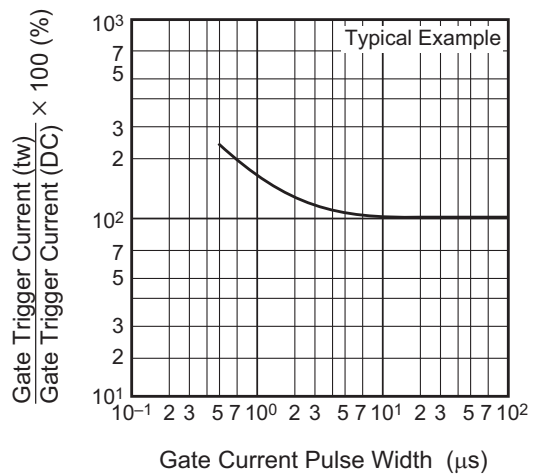
Turn-Off Time vs. Junction Temperature



Repetitive Peak Reverse Voltage vs. Junction Temperature



Gate Trigger Current vs. Gate Current Pulse Width



## Package Dimensions

**TO-220F**

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	—	2.0	Cu alloy

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A <sub>1</sub>	—	—	—
A <sub>2</sub>	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y <sub>1</sub>	—	—	—
ZD	—	—	—
ZE	—	—	—

## Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +A	CR6PM-12A
Lead form	Plastic Magazine (Tube)	50	Type name +A – Lead forming code	CR6PM-12A-A8

Note : Please confirm the specification about the shipping in detail.

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